IGBT

High speed IGBT in Trench and Fieldstop technology

IGW30N60H3

600V high speed switching series third generation

Data sheet

Industrial Power Control

IGW30N60H3

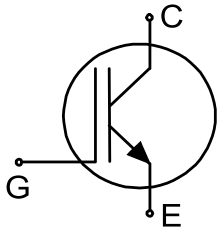
High speed switching series third generation

High speed IGBT in Trench and Fieldstop technology

Features:

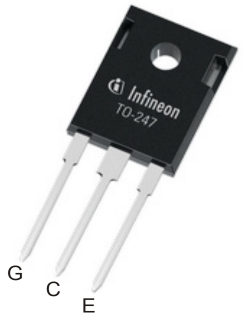
TRENCHSTOP^{TM} technology offering
- very low V_{CEsat}
- low EMI
- Very soft, fast recovery anti-parallel diode
- maximum junction temperature 175°C
- qualified according to JEDEC for target applications
- Pb-free lead plating; RoHS compliant
- complete product spectrum and PSpice Models:

http://www.infineon.com/igbt/



Applications:

- uninterruptible power supplies
- welding converters
- converters with high switching frequency



Key Performance and Package Parameters

Type	V_{CE}	I_C	V_{CEsat}, T_{vj}=25°C	T_{vjmax}	Marking	Package
IGW30N60H3	600V	30A	1.95V	175°C	G30H603	PG-TO247-3

Table of Contents

Maximum ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage, $T_{vj} \geq 25°C$	V_{CE}	600	V
DC collector current, limited by T_{vjmax} $T_C = 25°C$ $T_C = 100°C$	I_C	 60.0 30.0	A
Pulsed collector current, t_p limited by T_{vjmax}	I_{Cpuls}	120.0	A
Turn off safe operating area $V_{CE} \leq 600V$, $T_{vj} \leq 175°C$, $t_p = 1µs$	-	120.0	A
Gate-emitter voltage	V_{GE}	±20	V
Short circuit withstand time $V_{GE} = 15.0V$, $V_{CC} \leq 400V$ Allowed number of short circuits < 1000 Time between short circuits: ≥ 1.0s $T_{vj} = 150°C$	t_{SC}	 5	µs
Power dissipation $T_C = 25°C$ Power dissipation $T_C = 100°C$	P_{tot}	187.0 94.0	W
Operating junction temperature	T_{vj}	-40...+175	°C
Storage temperature	T_{stg}	-55...+150	°C
Soldering temperature, wave soldering 1.6 mm (0.063 in.) from case for 10s		 260	°C
Mounting torque, M3 screw Maximum of mounting processes: 3	M	0.6	Nm

Thermal Resistance

Parameter	Symbol	Conditions	Max. Value	Unit
Characteristic				
IGBT thermal resistance, junction - case	$R_{th(j-c)}$		0.80	K/W
Thermal resistance junction - ambient	$R_{th(j-a)}$		40	K/W

Electrical Characteristic, at $T_{vj} = 25°C$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Static Characteristic						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE} = 0V$, $I_C = 2.00mA$	600	-	-	V
Collector-emitter saturation voltage	V_{CEsat}	$V_{GE} = 15.0V$, $I_C = 30.0A$ $T_{vj} = 25°C$ $T_{vj} = 125°C$ $T_{vj} = 175°C$	 - - -	 1.95 2.30 2.50	 2.40 - -	V
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C = 0.43mA$, $V_{CE} = V_{GE}$	4.1	5.1	5.7	V
Zero gate voltage collector current	I_{CES}	$V_{CE} = 600V$, $V_{GE} = 0V$ $T_{vj} = 25°C$ $T_{vj} = 175°C$	 - -	 - -	 40.0 2000.0	µA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0V$, $V_{GE} = 20V$	-	-	100	nA
Transconductance	g_{fs}	$V_{CE} = 20V$, $I_C = 30.0A$	-	16.0	-	S

Electrical Characteristic, at T_{vj} = 25°C, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Dynamic Characteristic						
Input capacitance	C_{ies}	V_{CE} = 25V, V_{GE} = 0V, f = 1MHz	-	1630	-	pF
Output capacitance	C_{oes}		-	107	-	
Reverse transfer capacitance	C_{res}		-	50	-	
Gate charge	Q_G	V_{CC} = 480V, I_C = 30.0A, V_{GE} = 15V	-	165.0	-	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	L_E		-	13.0	-	nH
Short circuit collector current Max. 1000 short circuits Time between short circuits: ≥ 1.0s	$I_{C(SC)}$	V_{GE} = 15.0V, V_{CC} ≤ 400V, t_{SC} ≤ 5µs T_{vj} = 150°C	-	160	-	A

Switching Characteristic, Inductive Load

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic, at T_{vj} = 25°C						
Turn-on delay time	$t_{d(on)}$	T_{vj} = 25°C, V_{CC} = 400V, I_C = 30.0A, V_{GE} = 0.0/15.0V, r_G = 10.5Ω, $L\sigma$ = 95nH, $C\sigma$ = 67pF $L\sigma$, $C\sigma$ from Fig. E Energy losses include “tail” and diode (IKW30N60H3) reverse recovery.	-	21	-	ns
Rise time	t_r		-	33	-	ns
Turn-off delay time	$t_{d(off)}$		-	207	-	ns
Fall time	t_f		-	22	-	ns
Turn-on energy	E_{on}		-	0.94	-	mJ
Turn-off energy	E_{off}		-	0.44	-	mJ
Total switching energy	E_{ts}		-	1.38	-	mJ

Switching Characteristic, Inductive Load

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic, at T_{vj} = 175°C						
Turn-on delay time	$t_{d(on)}$	T_{vj} = 175°C, V_{CC} = 400V, I_C = 30.0A, V_{GE} = 0.0/15.0V, r_G = 10.5Ω, $L\sigma$ = 95nH, $C\sigma$ = 67pF $L\sigma$, $C\sigma$ from Fig. E Energy losses include “tail” and diode (IKW30N60H3) reverse recovery.	-	20	-	ns
Rise time	t_r		-	30	-	ns
Turn-off delay time	$t_{d(off)}$		-	239	-	ns
Fall time	t_f		-	23	-	ns
Turn-on energy	E_{on}		-	1.12	-	mJ
Turn-off energy	E_{off}		-	0.60	-	mJ
Total switching energy	E_{ts}		-	1.72	-	mJ

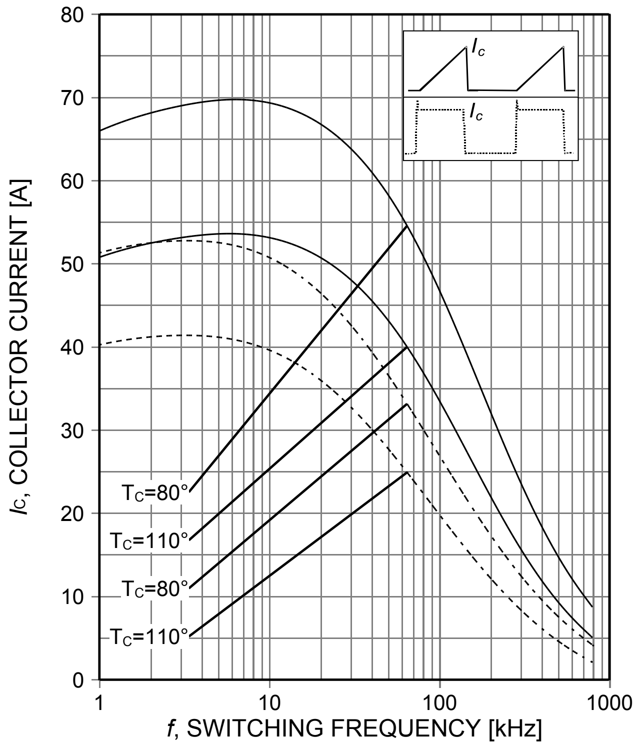


Figure 1. **Collector current as a function of switching frequency**
($T_j \leq 175°C$, $D=0.5$, $V_{CE}=400V$, $V_{GE}=15/0V$, $r_G=10,5\Omega$)

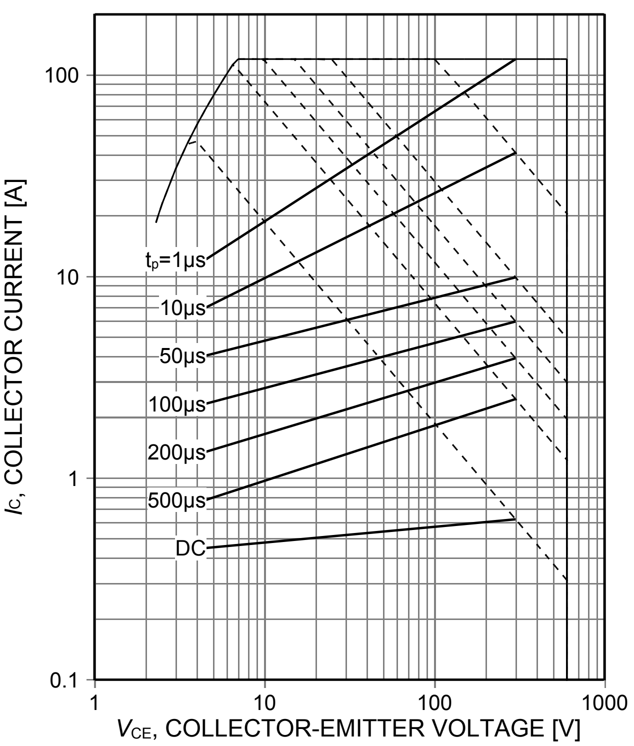


Figure 2. **Forward bias safe operating area**
($D=0$, $T_C=25°C$, $T_j \leq 175°C$; $V_{GE}=15V$)

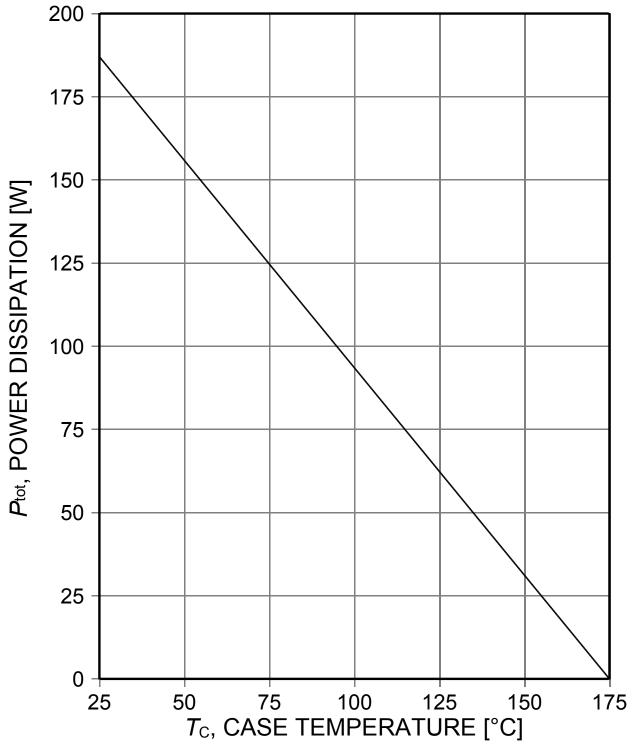


Figure 3. **Power dissipation as a function of case temperature**
($T_j \leq 175°C$)

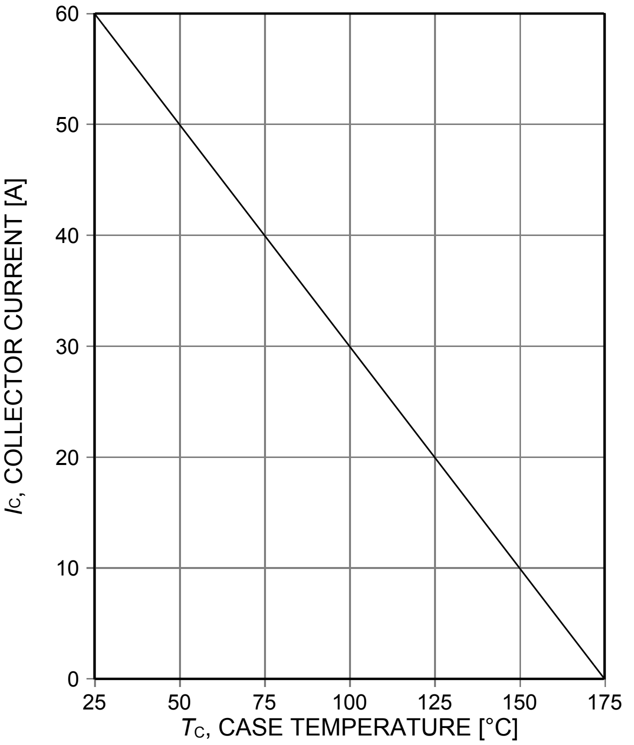


Figure 4. **Collector current as a function of case temperature**
($V_{GE} \geq 15V$, $T_j \leq 175°C$)

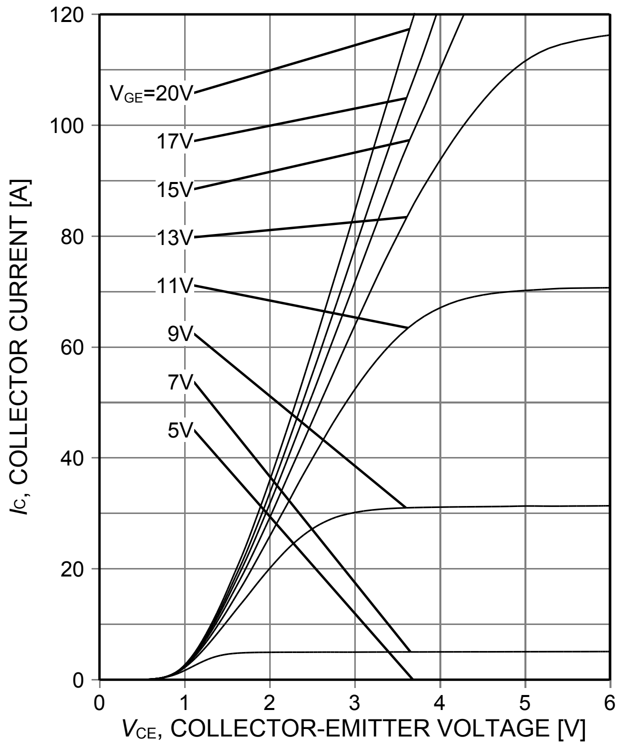


Figure 5. **Typical output characteristic**
(T_j=25°C)

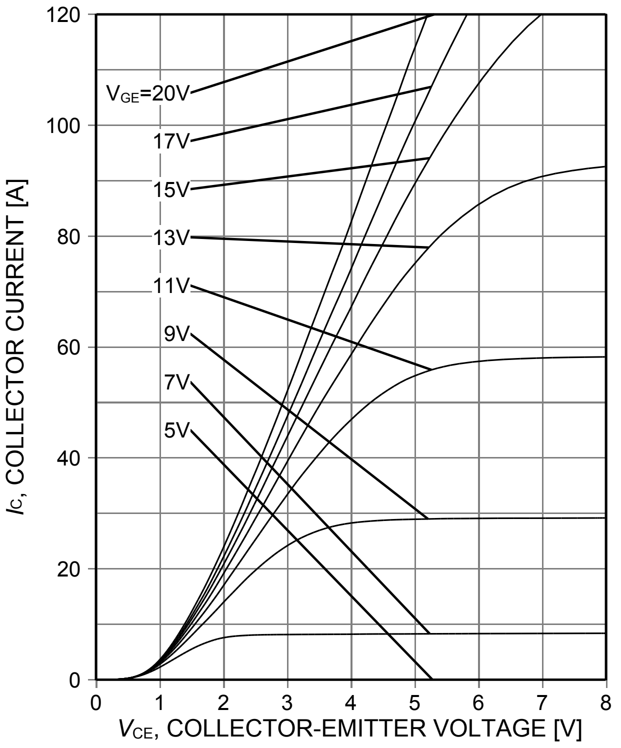


Figure 6. **Typical output characteristic**
(T_j=175°C)

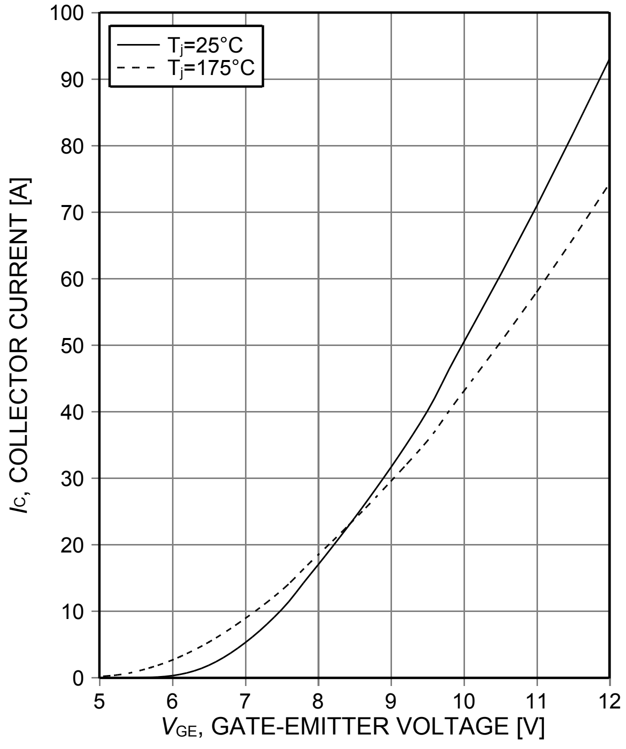


Figure 7. **Typical transfer characteristic**
(V_{CE}=20V)

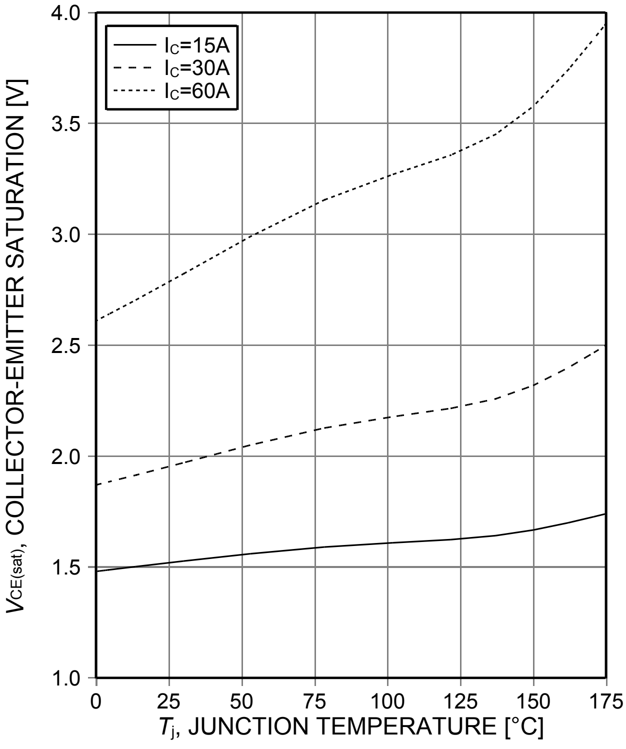


Figure 8. **Typical collector-emitter saturation voltage as a function of junction temperature**
(V_{GE}=15V)

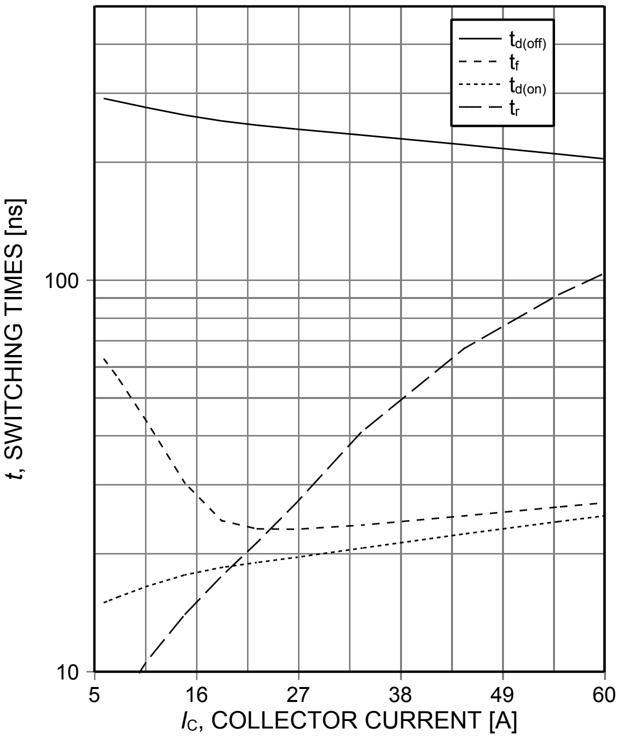


Figure 9. **Typical switching times as a function of collector current**
(ind. load, T_j=175°C, V_{CE}=400V, V_{GE}=15/0V, r_G=10,5Ω, test circuit in Fig. E)

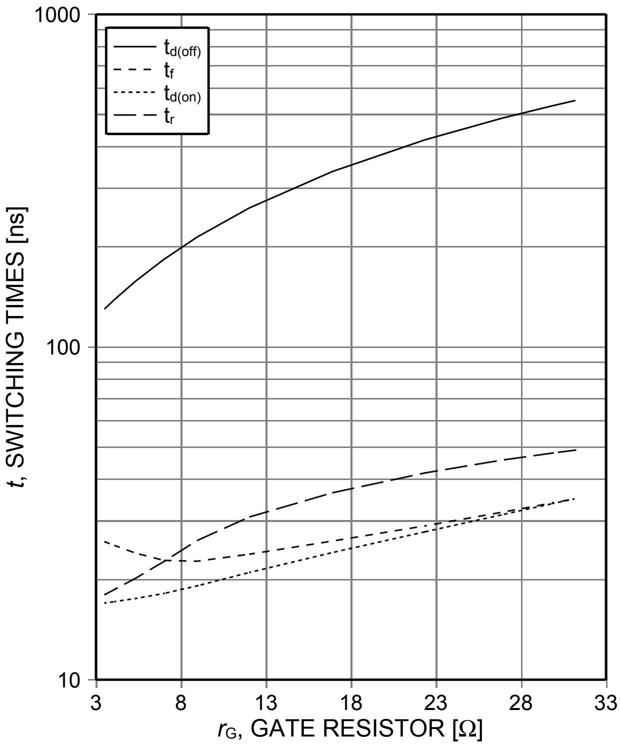


Figure 10. **Typical switching times as a function of gate resistor**
(ind. load, T_j=175°C, V_{CE}=400V, V_{GE}=15/0V, I_C=30A, test circuit in Fig. E)

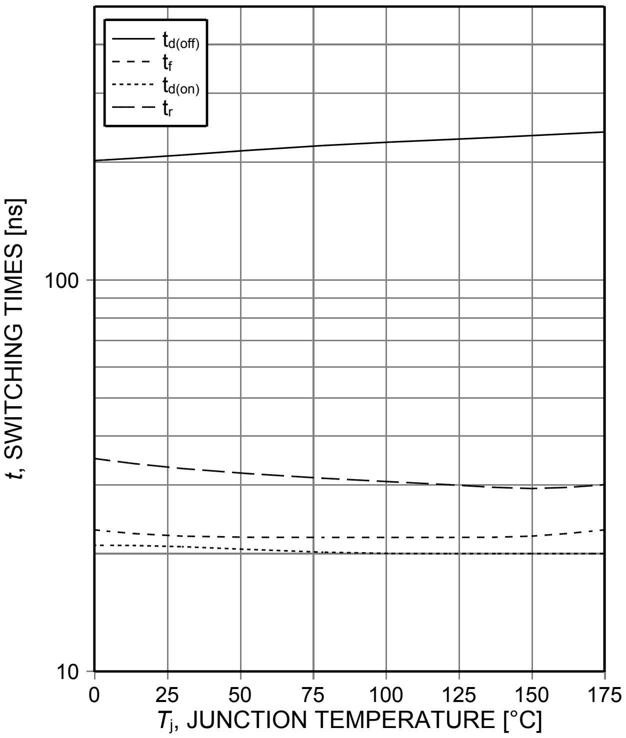


Figure 11. **Typical switching times as a function of junction temperature**
(ind. load, V_{CE}=400V, V_{GE}=15/0V, I_C=30A, r_G=10,5Ω, test circuit in Fig. E)

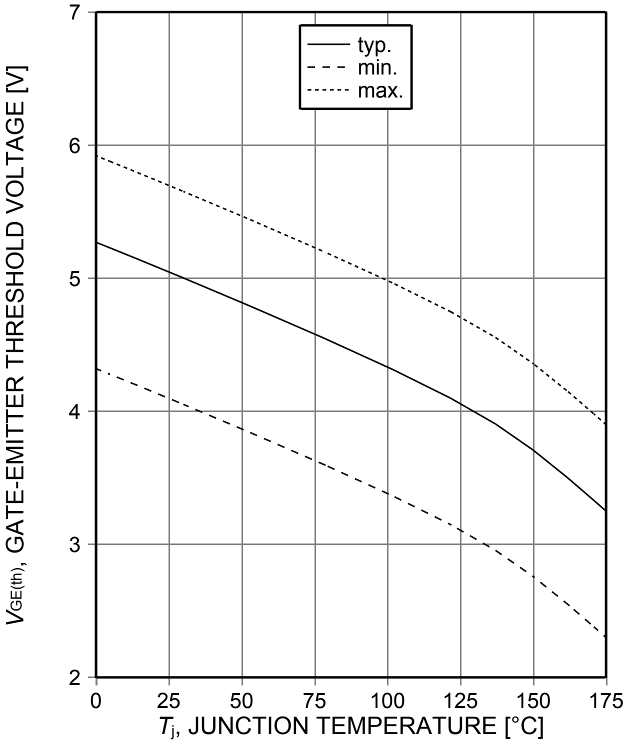
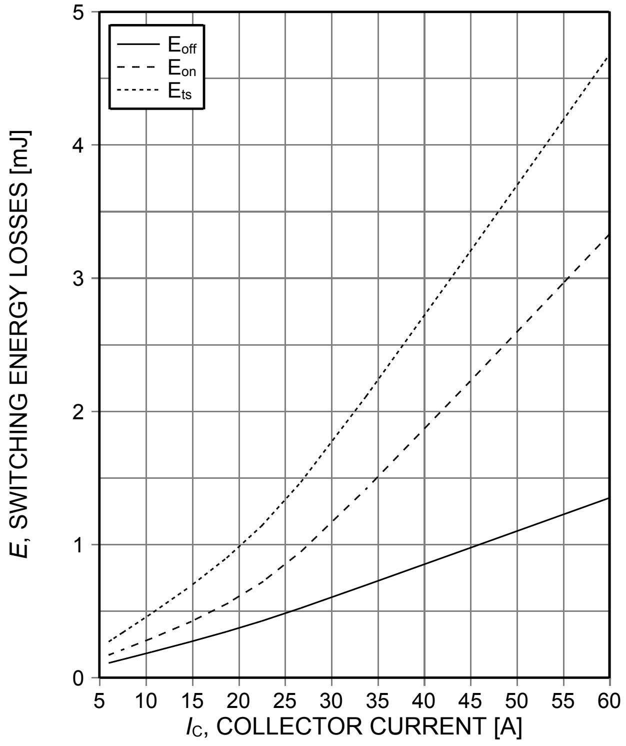


Figure 12. **Gate-emitter threshold voltage as a function of junction temperature**
(I_C=0.43mA)



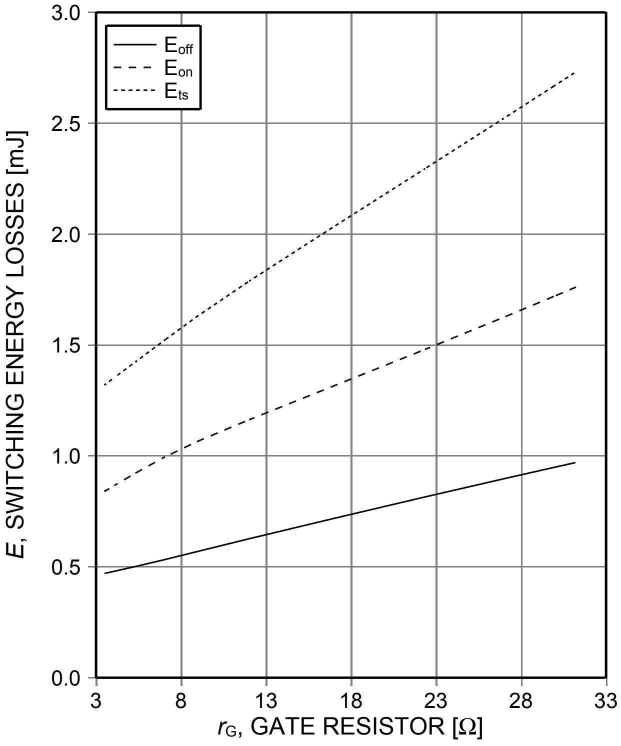
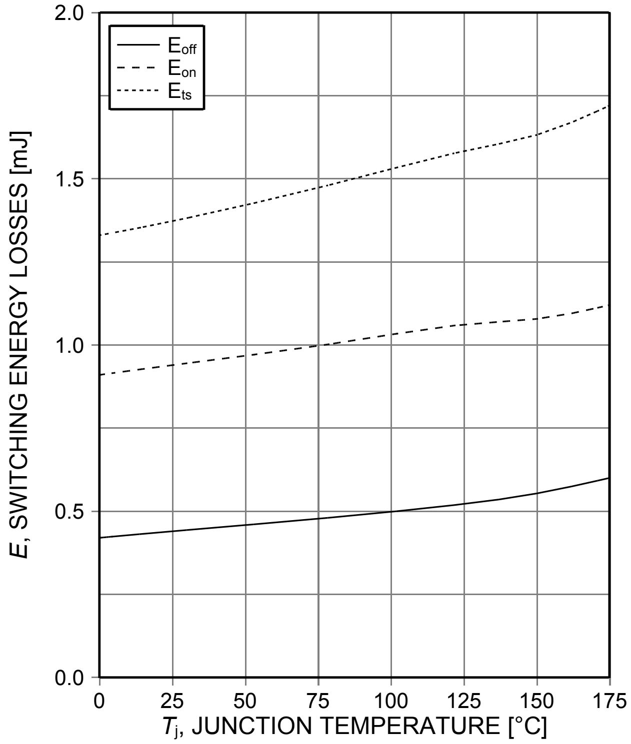


Figure 13. **Typical switching energy losses as a function of collector current**
(ind. load, T_j=175°C, V_{CE}=400V, V_{GE}=15/0V, r_G=10,5Ω, test circuit in Fig. E)

Figure 14. **Typical switching energy losses as a function of gate resistor**
(ind. load, T_j=175°C, V_{CE}=400V, V_{GE}=15/0V, I_C=30A, test circuit in Fig. E)



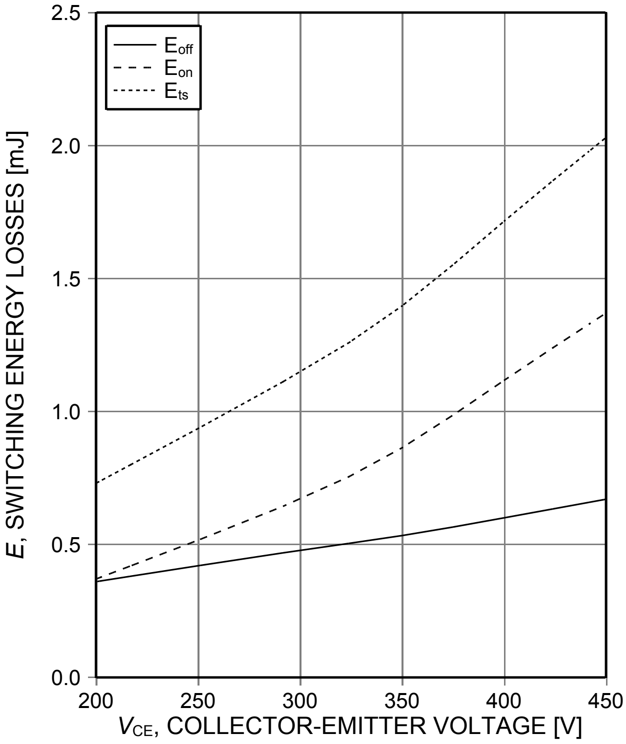


Figure 15. **Typical switching energy losses as a function of junction temperature**
(ind load, V_{CE}=400V, V_{GE}=15/0V, I_C=30A, r_G=10,5Ω, test circuit in Fig. E)

Figure 16. **Typical switching energy losses as a function of collector emitter voltage**
(ind. load, T_j=175°C, V_{GE}=15/0V, I_C=30A, r_G=10,5Ω, test circuit in Fig. E)

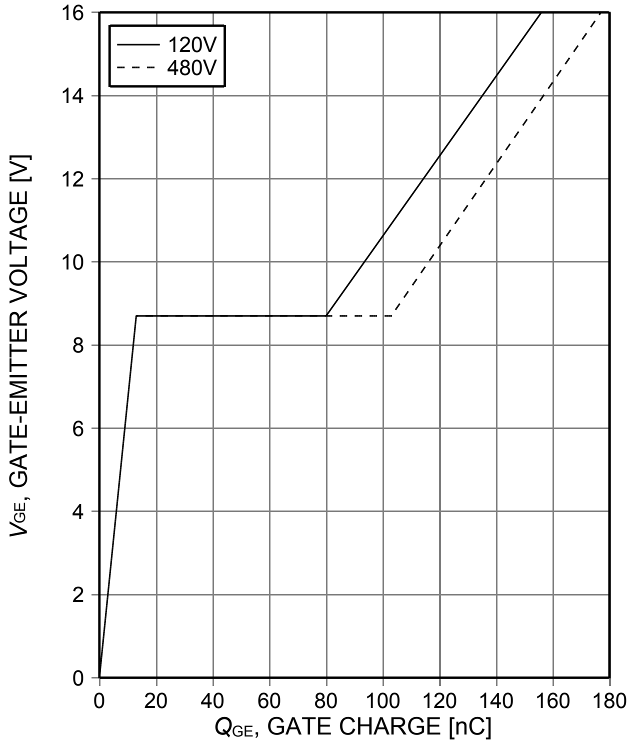


Figure 17. **Typical gate charge**
(I_C=30A)

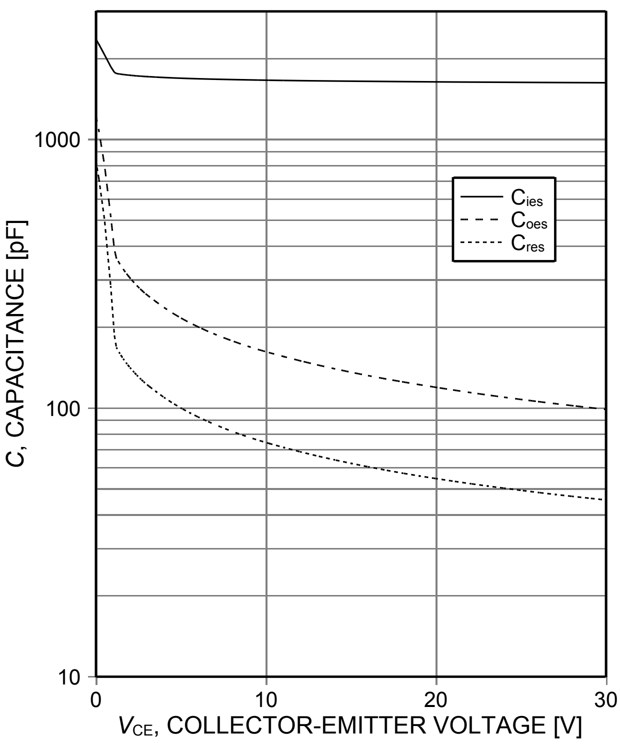


Figure 18. **Typical capacitance as a function of collector-emitter voltage**
(V_{GE}=0V, f=1MHz)

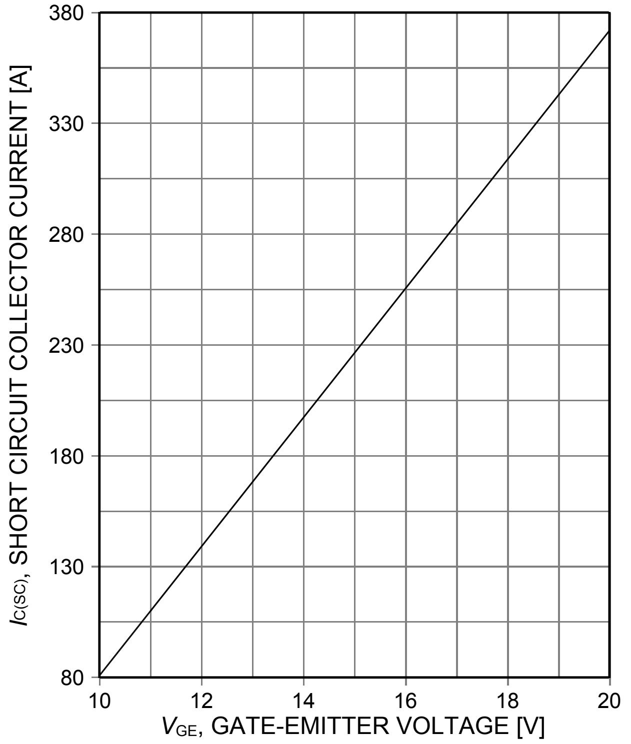


Figure 19. **Typical short circuit collector current as a function of gate-emitter voltage**
(V_{CE}≤400V, start atT_j=25°C)

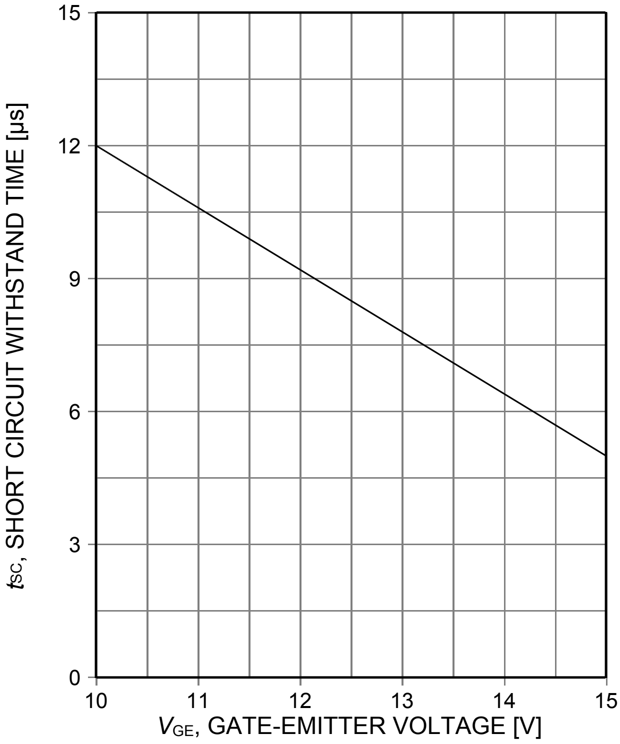


Figure 20. **Short circuit withstand time as a function of gate-emitter voltage**
(V_{CE}≤400V, start at T_j≤150°C)

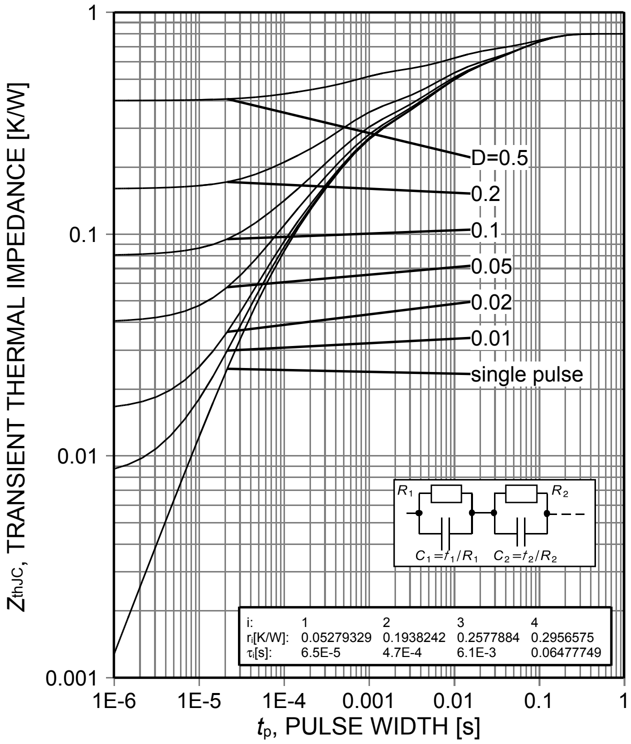
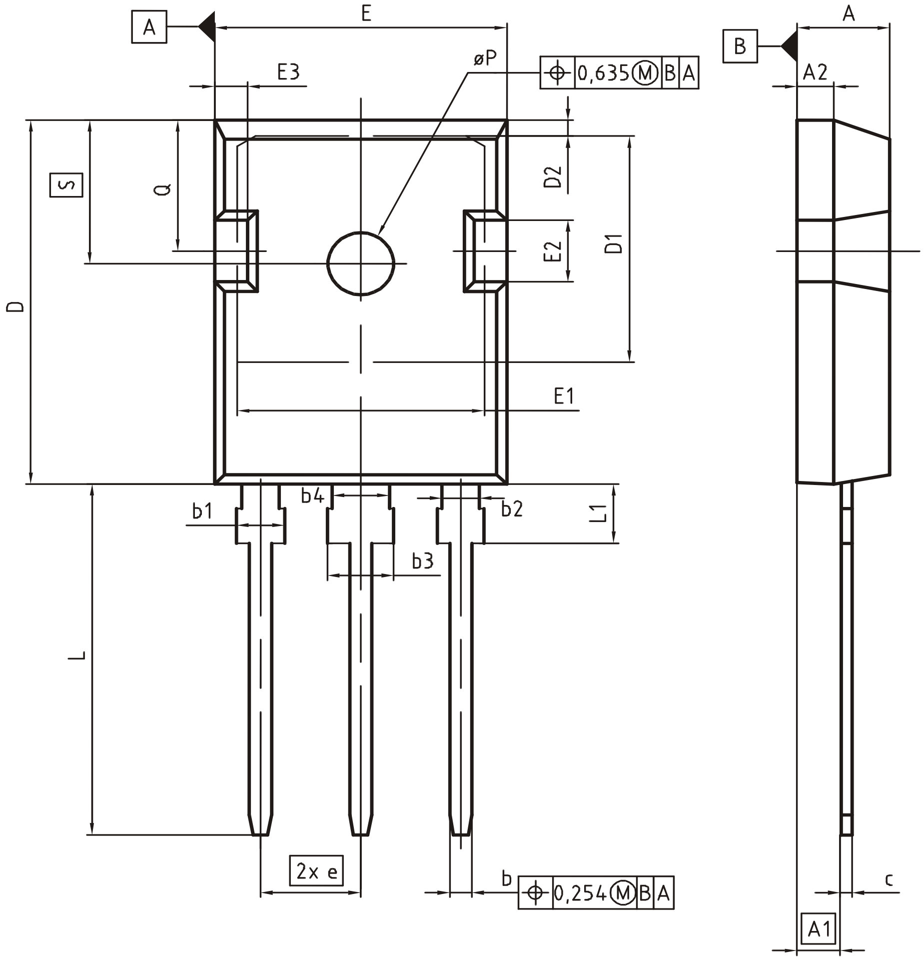


Figure 21. **IGBT transient thermal impedance**
(D=t_p/T)

PG-TO247-3



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.83	5.21	0.190	0.205
A1	2.27	2.54	0.089	0.100
A2	1.85	2.16	0.073	0.085
b	1.07	1.33	0.042	0.052
b1	1.90	2.41	0.075	0.095
b2	1.90	2.16	0.075	0.085
b3	2.87	3.38	0.113	0.133
b4	2.87	3.13	0.113	0.123
c	0.55	0.68	0.022	0.027
D	20.80	21.10	0.819	0.831
D1	16.25	17.65	0.640	0.695
D2	0.95	1.35	0.037	0.053
E	15.70	16.13	0.618	0.635
E1	13.10	14.15	0.516	0.557
E2	3.68	5.10	0.145	0.201
E3	1.00	2.60	0.039	0.102
e	5.44 (BSC)		0.214 (BSC)	
N	3		3	
L	19.80	20.32	0.780	0.800
L1	4.10	4.47	0.161	0.176
øP	3.50	3.70	0.138	0.146
Q	5.49	6.00	0.216	0.236
S	6.04	6.30	0.238	0.248

DOCUMENT NO.
Z8B00003327

SCALE 0 5 0 5 7.5mm

EUROPEAN PROJECTION

ISSUE DATE
09-07-2010

REVISION
05

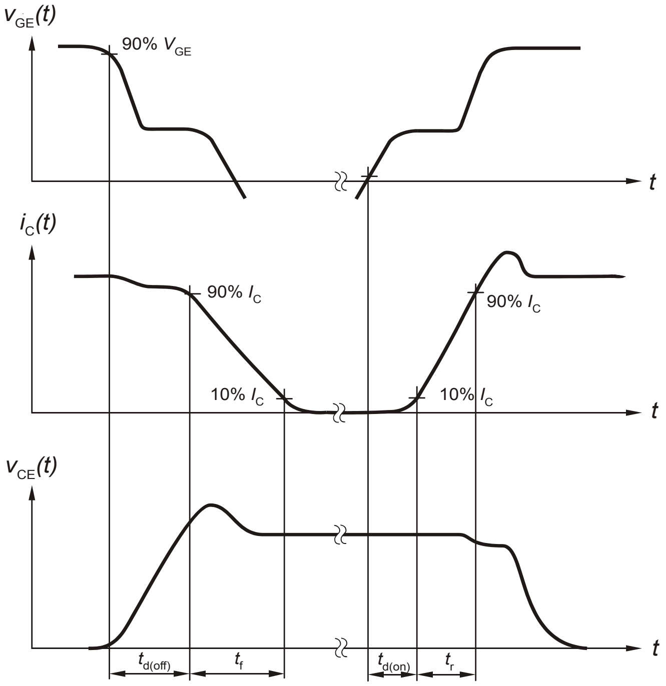


Figure A. Definition of switching times

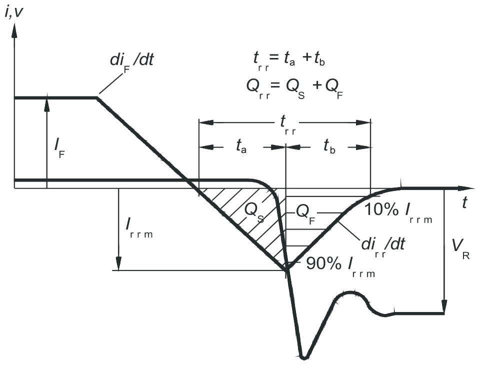


Figure C. Definition of diodes switching characteristics

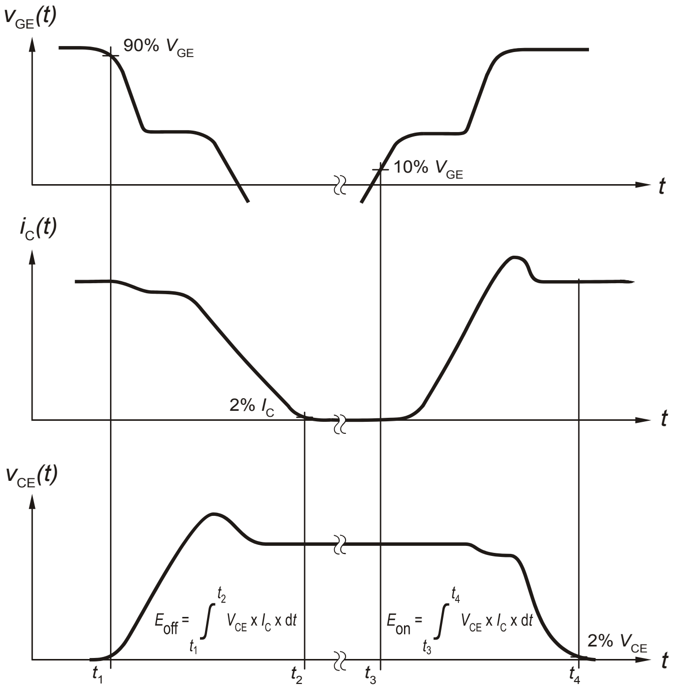


Figure B. Definition of switching losses

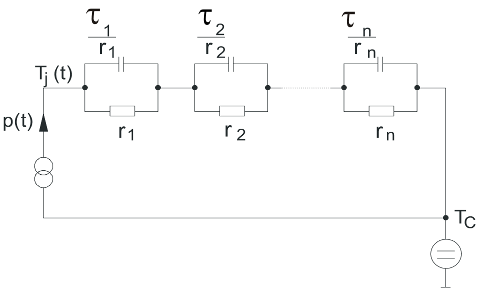


Figure D. Thermal equivalent circuit

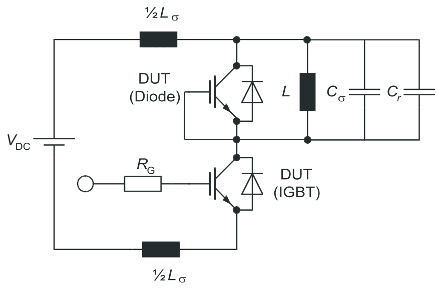


Figure E. Dynamic test circuit
Parasitic inductance L_σ,
Parasitic capacitor C_σ,
Relief capacitor C_r
(only for ZVT switching)

IGW30N60H3

High speed switching series third generation

Revision History

IGW30N60H3

Revision: 2014-03-12, Rev. 2.2

Previous Revision

Revision	Date	Subjects (major changes since last revision)
1.1	2010-07-26	Preliminary datasheet
2.1	2013-12-10	New value ICES max limit at 175°C
2.2	2014-03-12	Max ratings Vce, Tvj ≥ 25°C

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